FAIRCHILD

NDT014L N-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology.This very high density process is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes.Thesedevices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

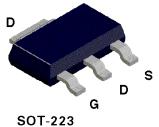
Features

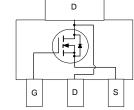
- $\begin{array}{c|c} \bullet & 2.8 \text{ A, } 60 \text{ V. } \text{R}_{\text{DS(ON)}} = 0.2 \ \Omega & @ \ \text{V}_{\text{GS}} = \ 4.5 \text{ V} \\ & \text{R}_{\text{DS(ON)}} = 0.16 \ \Omega & @ \ \text{V}_{\text{GS}} = \ 10 \text{ V.} \end{array}$
- High density cell design for extremely low R_{DS(ON)}.
- High power and current handling capability in a widely used surface mount package.

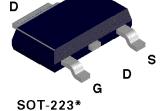
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(J23Z)

Absolute Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	NDT014L	Units
V _{DSS}	Drain-Source Voltage	60	V
V _{GSS}	Gate-Source Voltage	± 20	V
I _D	Drain Current - Continuous (Note 1a)	± 2.8	А
	- Pulsed	± 10	
P _D	Maximum Power Dissipation (Note 1a)	3	W
	(Note 1b)	1.3	
	(Note 1c)	1.1	
T_J,T _{STG}	Operating and Storage Temperature Range	-65 to 150	°C
THERMA	L CHARACTERISTICS		
R _{øja}	Thermal Resistance, Junction-to-Ambient (Note 1a)	a) 42	
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	12	°C/W

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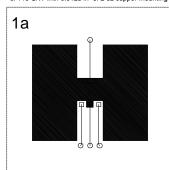
Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHA	RACTERISTICS				•	•	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$		60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$				25	μA
			$T_{J} = 55^{\circ}C$			250	μA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
ON CHAR	ACTERISTICS (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		1	1.5	3	V
			T _J = 125°C	0.8	1.1	2	
R _{DS(ON)}	Static Drain-Source On-Resistance	V_{GS} = 4.5 V, I_{D} = 2.8 A			0.17	0.2	Ω
			T _J = 125°C		0.22	0.36	
		$V_{GS} = 10 \text{ V}, \ I_{D} = 3.4 \text{ A}$			0.12	0.16	
I _{D(on)}	On-State Drain Current $V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$			5			А
		$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$		10			
G _{FS}	Forward Transconductance	$V_{GS} = 5 \text{ V}, \ I_{D} = 2.8 \text{ A}$			4.2		S
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ f = 1.0 MHz			214		pF
C _{oss}	Output Capacitance				70		pF
C _{rss}	Reverse Transfer Capacitance				27		pF
SWITCHIN	IG CHARACTERISTICS (Note 2)						
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 3 \text{ A},$ $V_{GEN} = 10 \text{ V}, \text{ R}_{GEN} = 12 \Omega$			6	12	ns
t,	Turn - On Rise Time				14	25	ns
t _{D(off)}	Turn - Off Delay Time				15	28	ns
t _r	Turn - Off Fall Time				10	18	ns
Q _g	Total Gate Charge	$V_{DS} = 10 \text{ V},$ $I_{D} = 2.8 \text{ A}, V_{GS} = 4.5 \text{ V}$			3.6	5	nC
Q _{gs}	Gate-Source Charge				0.8		nC
Q_{gd}	Gate-Drain Charge				1.4		nC

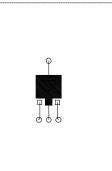
Electrical Characteristics (T _A = 25°C unless otherwise noted)							
Symbol	Parameter Conditions		Min	Тур	Max	Units	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
I _s	Maximum Continuous Drain-Source Diode Forward Current				2.3	А	
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 2.3 A (Note 2)$		0.85	1.3	V	
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, \text{ I}_{F} = 2.3 \text{ A } \text{dI}_{F}/\text{dt} = 100 \text{ A}/\mu\text{s}$			140	ns	

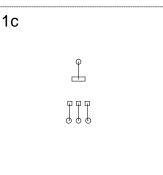
Notes:

Notes: 1. $P_D(t) = \frac{T_J - T_A}{R_{BJA}(t)} = \frac{T_J - T_A}{R_{BJC} - R_{BCA}(t)} = I_D^2(t) \times R_{DS(ON) \oplus T_J} R_{BA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BC} is guaranteed by design while R_{BCA} is defined by users. For general reference: Applications on 4.5"x5" FR-4 PCB under still air environment, typical R_{BA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BC} is guaranteed by design while R_{BCA} is defined by users. For general reference: Applications on 4.5"x5" FR-4 PCB under still air environment, typical R_{BA} is 55°C/W with 1 in² of 2 oz copper mounting pad. b. 95°C/W with 0.066 in² of 2 oz copper mounting pad. c. 110°C/W with 0.0123 in³ of 2 oz copper mounting pad.

1b

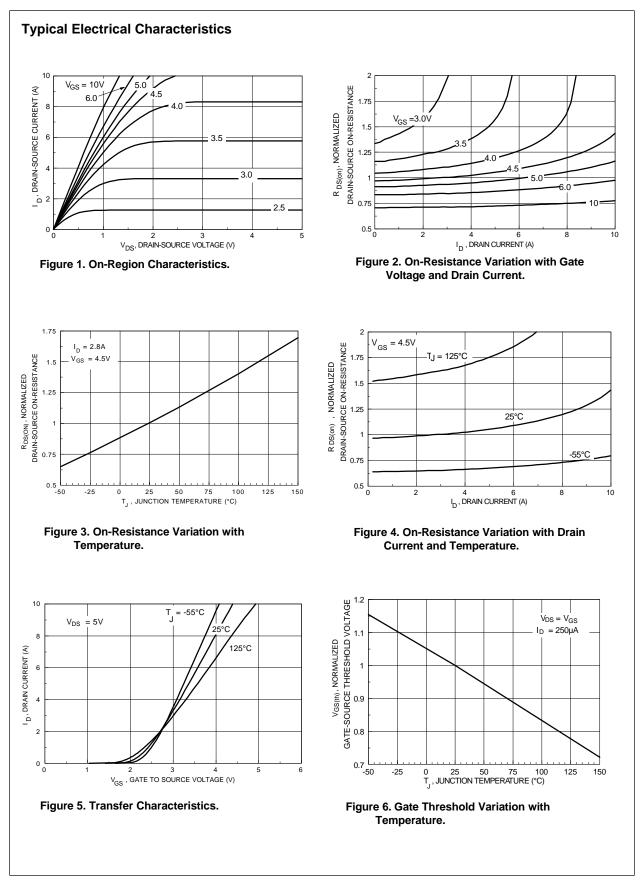


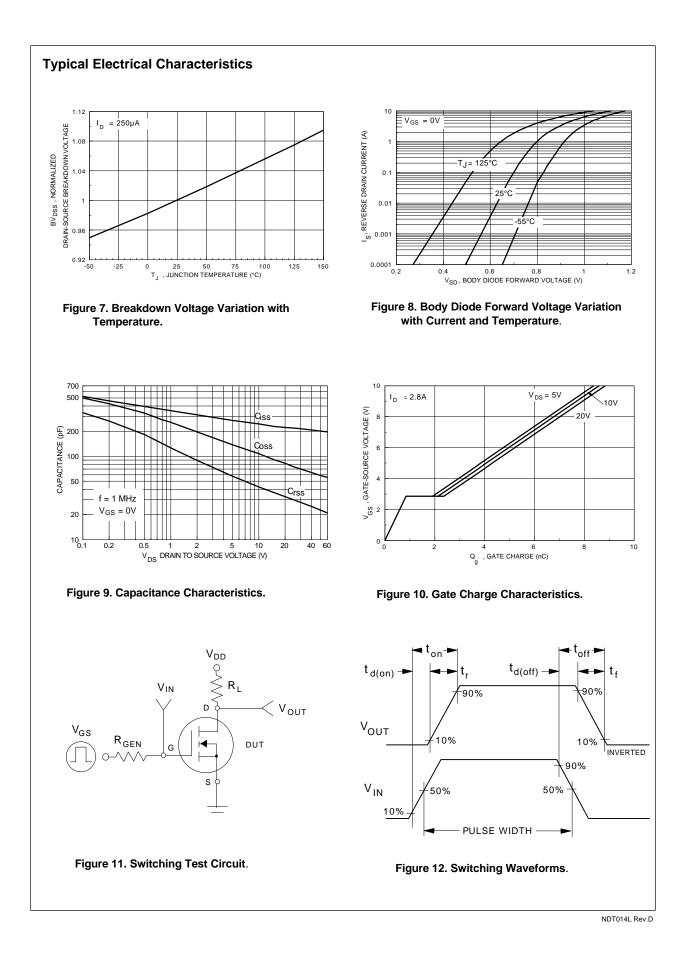


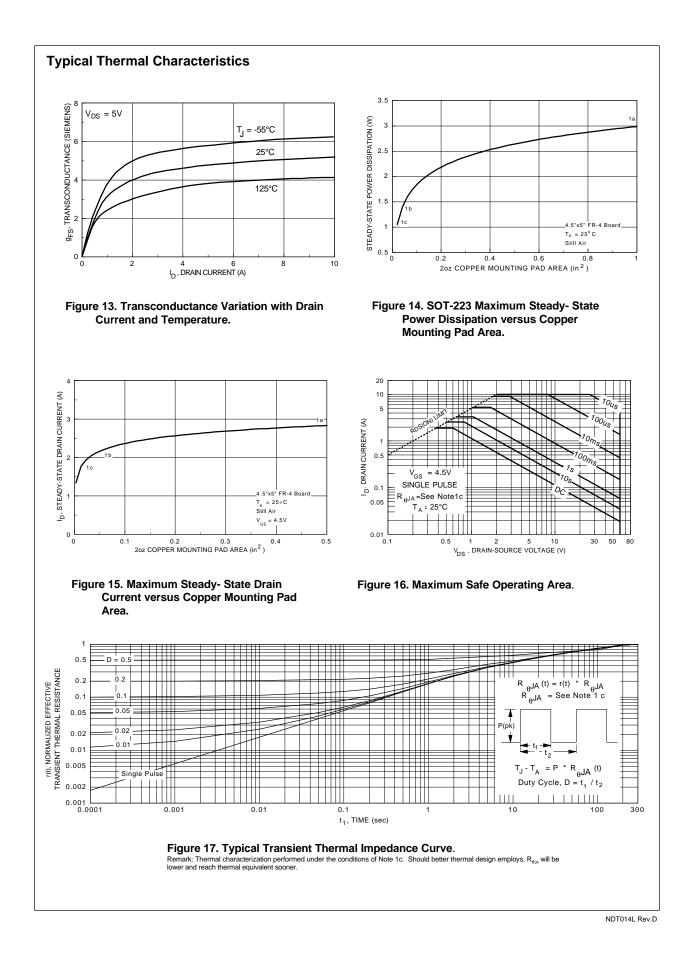


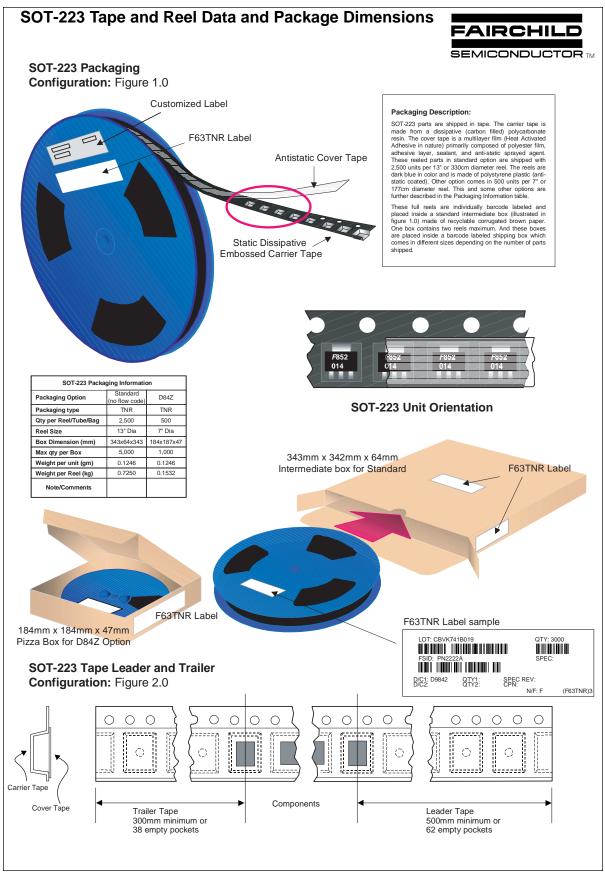
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

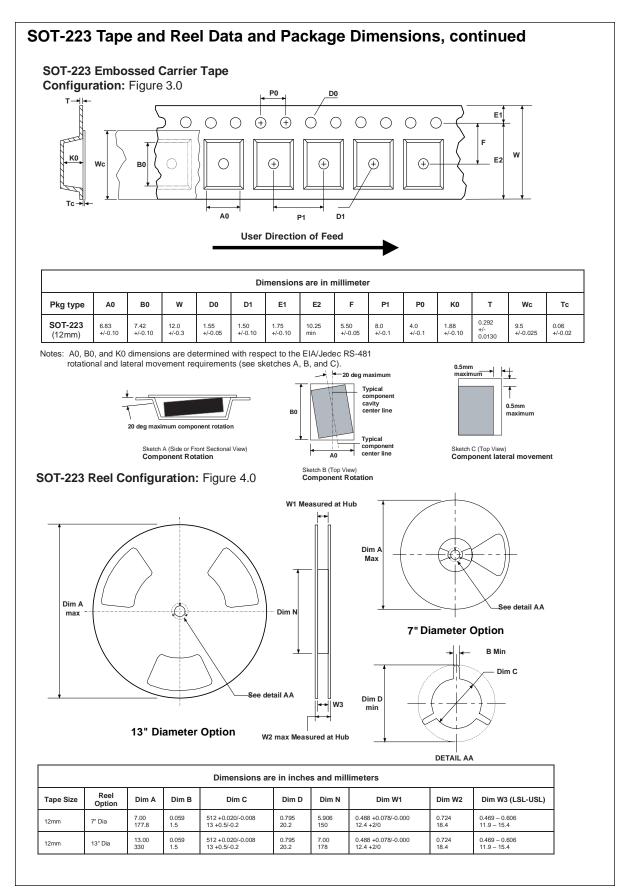


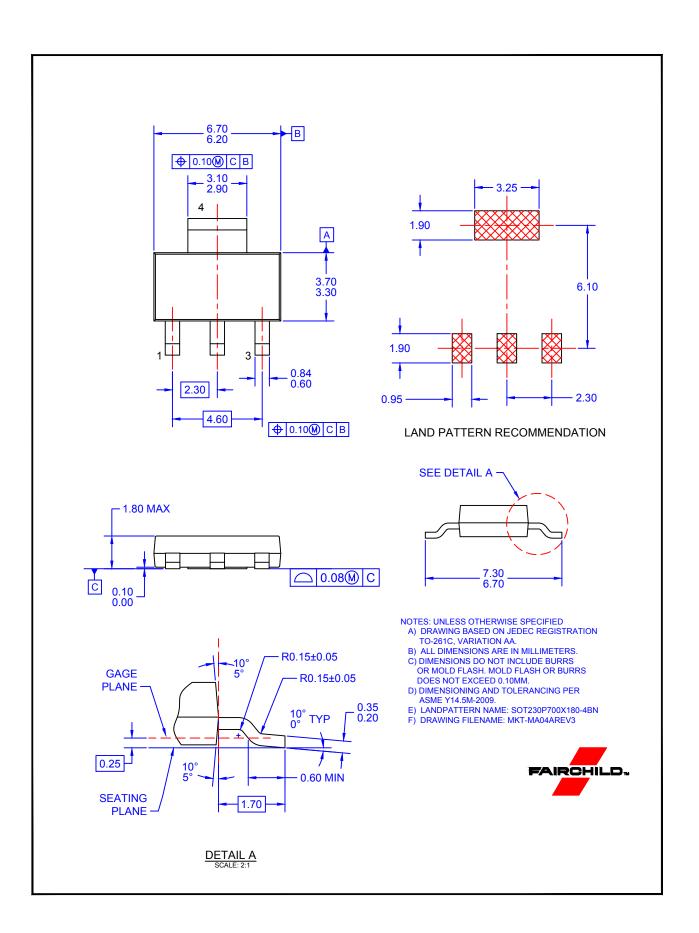






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